

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("6048758") or ("5960252").PN.	USPAT	OR	OFF	2004/11/12 18:05
S1	6009	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/13 09:12
S2	1	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:40
S3	0	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) with metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:16
S4	1	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj clusters)) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:18

S5	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:20
S6	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:22
S7	3	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:25
S8	647766	(metallic or(metal\$4 adj (cluster\$1 or element\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/20 14:58
S9	0	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/07 16:24
S10	0	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2 adj element) and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:30

S11	23348	((second and first and third) adj (semiconductor (film\$1 or layer\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:34
S12	0	((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1)))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:37
S13	3	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:39
S14	-1	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2) and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:41
S15	15096	getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:26
S16	2810	((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:43
S17	12	((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:44

S18	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:52
S19	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and ((first and second and third) adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:54
S20	5	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and (first adj (film\$1 or layers\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:27
S21	9	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and (semiconductor adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 18:56
S22	8595	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:28
S23	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:31
S24	1086	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:32
S25	715	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:32
S26	189	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4) and inert adj gas\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:33

S27	14	((((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4) and inert adj gas\$2) and (barrier adj (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/05 20:33
S28	6	("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/06/07 13:54
S29	4	((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639")).PN.) and barrier	US-PGPUB; USPAT	OR	OFF	2002/06/07 14:52
S30	3	(((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639")).PN.) and barrier) and block\$3	US-PGPUB; USPAT	OR	OFF	2002/06/07 14:51
S31	1	("6396147").PN.) and barrier	US-PGPUB; USPAT	OR	OFF	2002/06/07 14:53
S32	1	((("6396147"):PN.) and barrier) and amorphous	US-PGPUB; USPAT	OR	OFF	2002/06/07 14:53
S33	1	((("6396147").PN.) and barrier) and amorphous) and crystal\$4	US-PGPUB; USPAT	OR	OFF	2002/06/07 14:53
S34	1	(((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas	US-PGPUB; USPAT	OR	OFF	2002/06/07 14:54
S35	1	(((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas) and getter\$3	US-PGPUB; USPAT	OR	OFF	2002/06/07 14:54
S36	835	((438/166) or (438/486) or (438/476)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/06/08 13:58
S37	215	((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3	US-PGPUB; USPAT	OR	OFF	2002/06/08 14:43
S38	28	((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and (inert or noble) adj gas	US-PGPUB; USPAT	OR	OFF	2002/06/08 14:43
S39	9	((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and (inert or noble) adj gas) and barrier	US-PGPUB; USPAT	OR	OFF	2002/06/08 14:44
S40	0	("FOR0146").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/06/08 14:08
S41	0	("FOR0146").PN.	USOCR; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/10 19:02

S42	96	((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous	US-PGPUB; USPAT	OR	OFF	2002/06/08 14:43
S43	16	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous) and (inert or noble) adj gas	US-PGPUB; USPAT	OR	OFF	2002/06/08 14:43
S44	6	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous) and (inert or noble) adj gas and barrier	US-PGPUB; USPAT	OR	OFF	2002/06/08 14:44
S45	1	("6396147").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/06/10 17:37
S46	1	("5789284").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/06/10 17:37
S47	0	("FOR0146").PN.	USOCR; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/10 19:04
S48	9	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) with (anneal\$ with (electric adj current))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/21 16:53
S49	1	("20020086469").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/06/02 17:02
S50	19346	kim.in.	US-PGPUB; USPAT	OR	ON	2003/06/02 17:02
S51	8679	getter\$3	US-PGPUB; USPAT	OR	ON	2003/06/02 17:03
S52	44	kim.in. and getter\$3	US-PGPUB; USPAT	OR	ON	2003/06/02 17:03
S53	16337	getter\$3 or getter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/03 13:50
S54	2089	"semiconductor energy laboratory"	US-PGPUB; USPAT	OR	OFF	2003/06/03 13:52
S55	19706	tft or (thin adj film adj transistor)	US-PGPUB; USPAT	OR	ON	2003/06/03 13:58
S56	641	(getter\$3 or getter) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT	OR	ON	2003/06/03 14:00
S57	248	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory"	US-PGPUB; USPAT	OR	ON	2003/06/03 14:00

S58	40	((((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<"20010216") and "438"/\$.ccls.	US-PGPUB; USPAT	OR	ON	2003/06/03 14:02
S59	111	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<"20010216"	US-PGPUB; USPAT	OR	ON	2003/06/03 18:03
S60	32627	ozone	US-PGPUB; USPAT	OR	ON	2003/06/03 18:02
S61	110	((((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<"20010216")	US-PGPUB; USPAT	OR	ON	2003/06/03 18:03
S62	3	ozone and (((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<"20010216")	US-PGPUB; USPAT	OR	ON	2003/06/03 18:12
S63	66319	deioniz\$3	US-PGPUB; USPAT	OR	ON	2003/06/03 18:13
S64	0	((((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<"20010216") and deioniz\$3	US-PGPUB; USPAT	OR	ON	2003/06/03 18:13
S65	556	((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/06/06 12:37
S66	18319	amorphous\$3 and crystal\$8 and laser	US-PGPUB; USPAT	OR	ON	2003/06/06 12:38
S67	692277	barrier or (oxide or nitride or oxynitride)	US-PGPUB; USPAT	OR	ON	2003/06/06 12:38
S68	61	((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser))	US-PGPUB; USPAT	OR	ON	2003/06/06 12:38
S69	57	((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))	US-PGPUB; USPAT	OR	ON	2003/06/06 14:19

S70	57	((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))	US-PGPUB; USPAT	OR	ON	2003/06/06 14:22
S71	5183	catalytic near metal	US-PGPUB; USPAT	OR	ON	2003/06/06 14:24
S72	1	(((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))) and (catalytic near metal)	US-PGPUB; USPAT	OR	ON	2003/06/06 14:21
S73	112610	amorphous\$3	US-PGPUB; USPAT	OR	ON	2003/06/06 14:22
S74	505011	crystal\$8	US-PGPUB; USPAT	OR	ON	2003/06/06 14:23
S75	260315	laser	US-PGPUB; USPAT	OR	ON	2003/06/06 14:23
S76	692277	barrier or (oxide or nitride or oxynitride)	US-PGPUB; USPAT	OR	ON	2004/04/13 09:13
S77	28707	(catalytic or cluster or element) near metal	US-PGPUB; USPAT	OR	ON	2003/06/06 14:25
S78	2556	crystal\$8 same ((catalytic or cluster or element) near metal)	US-PGPUB; USPAT	OR	ON	2003/06/06 14:25
S79	1285	(crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3	US-PGPUB; USPAT	OR	ON	2003/06/06 14:25
S80	709	((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser	US-PGPUB; USPAT	OR	ON	2003/06/06 14:26
S81	676	(((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser) and (barrier or (oxide or nitride or oxynitride))	US-PGPUB; USPAT	OR	ON	2003/06/06 14:26
S82	8423	getter or gettering	US-PGPUB; USPAT	OR	ON	2003/06/06 14:26
S83	233	((((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)	US-PGPUB; USPAT	OR	ON	2003/06/06 14:45

S84	5636607	(fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)	US-PGPUB; USPAT	OR	ON	2003/06/06 14:50
S85	124463	((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8	US-PGPUB; USPAT	OR	ON	2003/06/06 14:51
S86	29298	amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)	US-PGPUB; USPAT	OR	ON	2003/06/06 14:51
S87	22525	(amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))	US-PGPUB; USPAT	OR	ON	2003/06/06 14:51
S88	690	((amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)	US-PGPUB; USPAT	OR	ON	2003/06/06 14:52
S89	531	(((amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)) and laser	US-PGPUB; USPAT	OR	ON	2003/06/06 14:52
S90	133656	(barrier or (oxide or nitride or oxynitride)) near (film or layer)	US-PGPUB; USPAT	OR	ON	2003/06/06 15:23

S91	14785	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)	US-PGPUB; USPAT	OR	ON	2003/06/06 15:23
S92	6367	(((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3	US-PGPUB; USPAT	OR	ON	2003/06/06 15:24
S93	614	(((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3) and (getter or gettering)	US-PGPUB; USPAT	OR	ON	2003/06/06 15:24
S94	511	((((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3) and (getter or gettering)) and laser	US-PGPUB; USPAT	OR	ON	2003/06/06 15:24
S95	44	"5821138".URPN.	USPAT	OR	OFF	2003/06/06 15:49
S96	5	("4838654" "5376561" "5488012" "5529937" "5618739").PN.	USPAT	OR	OFF	2003/06/06 15:54
S97	13	("4024626" "4759610" "4771016" "4838654" "4885616" "4906587" "4968638" "4980308" "4984033" "5110748" "5206749" "5256562" "5455187").PN.	USPAT	OR	OFF	2003/06/06 15:54

S98	13	("4024626" "4759610" "4771016" "4838654" "4885616" "4906587" "4968638" "4980308" "4984033" "5110748" "5206749" "5256562" "5455187").PN.	USPAT	OR	OFF	2003/06/06 15:54
S99	0	"6337259".URPN.	USPAT	OR	OFF	2003/06/06 16:14
S100	1	"6140166".PN.	USPAT	OR	OFF	2003/06/06 16:14
S101	0	"6337259".URPN.	USPAT	OR	OFF	2003/06/06 16:15
S102	0	"6376336".URPN.	USPAT	OR	OFF	2003/06/06 17:06
S103	30	("3936858" "4498227" "5194395" "5244819" "5272104" "5443661" "5453153" "5501993" "5646053" "5753560" "5773152" "5795809" "5807771" "5818085" "5882990" "5899732" "5926727" "5929508" "5965917" "5976956" "6001711" "6010950" "6013584" "6022793" "6024888" "6083324" "6093624" "6100202" "6114223" "6133123").PN.	USPAT	OR	OFF	2003/06/06 17:06
S104	1	("5605847").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/06/15 11:57
S105	1	("6097037").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/06/15 11:57
S106	1	("6337259").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/06/15 12:10
S107	36	funai.in.	US-PGPUB; USPAT	OR	OFF	2003/06/15 16:13
S108	1	("5550070").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/06/15 16:49
S109	7255	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/20 14:20

S11 0	9600	noble near gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:17
S11 1	260833	anneal or heat near2 treatment	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:18
S11 2	12617	getter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:50
S11 3	205	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and getter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:20
S11 4	5	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and getter) and (noble near gas)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:19
S11 5	1598	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (anneal or heat near2 treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:21
S11 6	66	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (noble near gas)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:33
S11 7	56	(438/310).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/20 14:44

S11 8	230662	helium or neon or argon or krypton or xenon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:05
S11 9	1114	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:46
S12 0	424	((((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)) and (anneal or heat near2 treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:46
S12 1	30	(((((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)) and (anneal or heat near2 treatment)) and getter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:46
S12 2	16843	getter or gettering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:50
S12 3	3575	(helium or neon or argon or krypton or xenon) and (getter or gettering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:51
S12 4	1152	((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:51
S12 5	711655	(metallic or(metal\$4 adj (cluster\$1 or element\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:58

S12 6	579	((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and ((metallic or(metal\$4 adj (cluster\$1 or element\$1))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:59
S12 7	1303417	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 14:59
S12 8	464	(((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and ((metallic or(metal\$4 adj (cluster\$1 or element\$1)))))) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 15:00
S12 9	210593	amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 15:00
S13 0	305	((((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and ((metallic or(metal\$4 adj (cluster\$1 or element\$1)))))) and semiconductor) and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/20 15:36
S13 1	5	("5696003").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/20 15:36
S13 2	35	"5696003".URPN.	USPAT	OR	OFF	2003/11/20 15:37
S13 3	17	("3783049" "4068020" "4309223" "5147826" "5275851" "5278093" "5289030" "5403772" "5481121" "5488000" "5501989" "5508533" "5529937" "5531182" "5534716" "5543352" "5569610").PN.	USPAT	OR	OFF	2003/11/20 15:58
S13 4	37	"5696003"	US-PGPUB; USPAT	OR	OFF	2003/11/20 16:22
S13 5	1	((("5696003").PN.) and (helium or neon or argon or krypton or xenon)	US-PGPUB; USPAT	OR	OFF	2003/11/20 16:23
S13 6	1	("5505070").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/11/20 16:48

S13 7	1990466	(He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:13
S13 8	51494	crystallize or crystalling	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:14
S13 9	82959	polycrystalline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:15
S14 0	15068	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) and (crystallize or crystallizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:29
S14 1	1413	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) and (crystallize or crystallizing) and polycrystalline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:15
S14 2	14	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near (crystallize or crystallizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:29
S14 3	139342	implant or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:35
S14 4	230817	(implant or implanting) or (dope or doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:36
S14 5	467	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:36
S14 6	2	(((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))) same (crystallize or crystallizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:38

S14 7	15	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))) and (crystallize or crystallizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:38
S14 8	1	("6391690").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/11/21 13:08
S14 9	5986	getter	US-PGPUB; USPAT	OR	OFF	2003/11/21 13:08
S15 0	0	(("6391690").PN.) and getter	US-PGPUB; USPAT	OR	OFF	2003/11/21 13:08
S15 1	1	"6337259"	US-PGPUB; USPAT	OR	OFF	2003/11/21 13:19
S15 2	1	laser and "6337259"	US-PGPUB; USPAT	OR	OFF	2003/11/21 13:19
S15 3	1	("5696003").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/11/21 13:41
S15 4	7538	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/13 09:12
S15 5	783211	barrier or (oxide or nitride or oxynitride)	US-PGPUB; USPAT	OR	ON	2004/04/13 09:15
S15 6	400286	(barrier or (oxide or nitride or oxynitride)) near2 (film or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:16
S15 7	147288	semiconductor near (film or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:16
S15 8	17881	getter or gettering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:16
S15 9	29458	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:16

S16 0	907	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:16
S16 1	122	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:20
S16 2	29458	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:20
S16 3	2602	Semiconductor adj energy adj laboratory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:22
S16 4	2542	(Semiconductor adj energy adj laboratory) not (((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:22
S16 5	62	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering))) not (Semiconductor adj energy adj laboratory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:34

S16 6	0	second near semiconductor near2 (film or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:38
S16 7	8543	second near semiconductor near2 (film or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:38
S16 8	1239	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:39
S16 9	80	(((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:39
S17 0	43	((((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)) not (Semiconductor adj energy adj laboratory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:39
S17 1	4	((((((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)) not (Semiconductor adj energy adj laboratory)) and (((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:40
S17 2	4	Semiconductor adj energy adj laboratories	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/18 18:47
S17 3	2600	Semiconductor adj energy adj laboratory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/18 18:51

S17 4	17891	getter or gettering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 18:51
S17 5	571	(Semiconductor adj energy adj laboratory) and (getter or gettering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 18:51
S17 6	191804	inert adj gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 18:52
S17 7	205	((Semiconductor adj energy adj laboratory) and (getter or gettering)) and (inert adj gas)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 18:52
S17 8	204382	semiconductor near2 (film or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 18:52
S17 9	205	(((Semiconductor adj energy adj laboratory) and (getter or gettering)) and (inert adj gas)) and (semiconductor near2 (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 19:05
S18 0	97068	barrier near2 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 19:06
S18 1	55	(((Semiconductor adj energy adj laboratory) and (getter or gettering)) and (inert adj gas)) and (semiconductor near2 (film or layer))) and (barrier near2 (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 19:26
S18 2	2	("6048758") or ("5248630").PN.	USPAT; USOCR	OR	OFF	2004/04/19 15:05
S18 3	79004	ozone	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/19 15:05

S18 4	263967	oxidize or oxidizing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/19 15:06
S18 5	9070	ozone same (oxidize or oxidizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/19 15:06
S18 6	960	ozone near (oxidize or oxidizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/19 15:07
S18 7	1380328	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/19 15:07
S18 8	35	(ozone near (oxidize or oxidizing)) same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/19 15:08
S18 9	9	(("5888858") or ("5663077") or ("5529937") or ("5654203")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/07/13 10:39
S19 0	4	(("5888858") or ("5663077") or ("5529937") or ("5654203")).PN.	USPAT; USOCR	OR	OFF	2004/07/13 10:39
S19 1	10922	noble near2 gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 10:39
S19 2	0	((("5888858") or ("5663077") or ("5529937") or ("5654203")).PN.) and (noble near2 gas)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 10:39
S19 3	248313	helium or neon or argon or krypton or xenon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:25

S19 4	2	(helium or neon or argon or krypton or xenon) and (((("5888858") or ("5663077") or ("5529937") or ("5654203")).PN.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 11:07
S19 5	318	electric near2 field near5 (helium or neon or argon or krypton or xenon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 11:11
S19 6	1395070	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 11:12
S19 7	112	(electric near2 field near5 (helium or neon or argon or krypton or xenon)) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 11:12
S19 8	509218	crystall\$8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 11:13
S19 9	20	((electric near2 field near5 (helium or neon or argon or krypton or xenon)) and semiconductor) and crystall\$8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/13 11:13
S20 0	1	("6048758").PN.	USPAT; USOCR	OR	OFF	2004/11/07 16:23
S20 1	8133	inert near-gas\$3 same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:27
S20 2	8133	(inert near gas\$3) same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:24
S20 3	336	((inert near gas\$3) same semiconductor) and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:24
S20 4	229	(((inert near gas\$3) same semiconductor) and getter\$3) and (helium or neon or argon or krypton or xenon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:25

S20 5	63	((inert near gas\$3) near element) same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:33
S20 6	3	((inert near gas\$3) near element) same ((implant\$5 or add\$3 or dop\$3) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:36
S20 7	32	((inert near gas\$3) near element) same ((implant\$5 or add\$3 or dop\$3) same(silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/07 16:37
S20 8	2404830	semiconductor energy laboratory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/03 13:51
S20 9	8294	(getter\$3 or getter) not "semiconductor energy laboratory"	US-PGPUB; USPAT	OR	OFF	2003/06/03 13:58
S21 0	110	(((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<"20010216") and "6"	US-PGPUB; USPAT	OR	ON	2003/06/03 18:13
S21 1	62884	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/21 12:35
S21 2	405320	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) smae (second near semiconductor near2 (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/13 09:38
S21 3	55	(((Semiconductor adj energy adj laboratory) and (getter or gettering)) and (inert adj gas)) and (semiconductor near2 (film or layer))) and (barrier near2 (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/18 19:05